

# Dual Laser-assisted Glass Frit Encapsulation for Efficient and Long-Term Stable N-I-P Perovskite Solar Cell

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## Abstract

According to international standards (IEC 61646 climatic chamber tests), photovoltaic devices must be long-term stable under a temperature range of -40 C to 85 C and to a relative humidity of 85%. For this reason, perovskite solar cells (PSCs) must be manufactured from stable materials and encapsulated appropriately to avoid degradation due to moisture and oxygen exposure. Laser-assisted glass frit encapsulation has been successfully used to achieve long-term stable PSCs with n-i-p and HTM-free structures. The laser-sealing process can be achieved with a single laser beam or dual laser beams. The laser-assisted glass frit encapsulation method was initially reported for hermetically encapsulated HTM-free PSCs at *ca.* 100 C using a single laser beam. Later, an advanced novel dual laser beam glass frit sealing process was developed and optimized to hermetically encapsulate n-i-p PSCs, allowing to decrease the process temperature to 65  5 C. The present work reports the use of advanced laser-assisted glass frit encapsulation using dual laser beams for encapsulating PSCs devices with different electron transport layers (ETL) and hole transport layers (HTL). Preliminary results of encapsulated n-i-p PSCs with poly[bis(4-phenyl)(2,4,6-trimethylphenyl) amine] (PTAA) as HTL at a process temperature of 65  5 C for 1 h, presented a reduction in average power conversion efficiency (PCE) from 14.18  2.4% to 12.32  0.90%. The reduction in performance was mainly due to a decrease in fill factor (FF) from 0.67  0.09 to 0.56  0.04. It was registered a slight decrease in open circuit voltage ( $V_{OC}$ ) from 1.01  0.03 V to 0.99  0.02 V, while the short circuit current density ( $J_{SC}$ ) increased from 20.73  0.77 mA cm<sup>-2</sup> to 21.97  0.46 mA cm<sup>-2</sup>. The performance loss of *ca.* 10% is related to the long exposure to heat during the laser sealing process.

## Keywords

Hermetic Encapsulation, Dual Laser, Glass Frit, Perovskite Solar Cell

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